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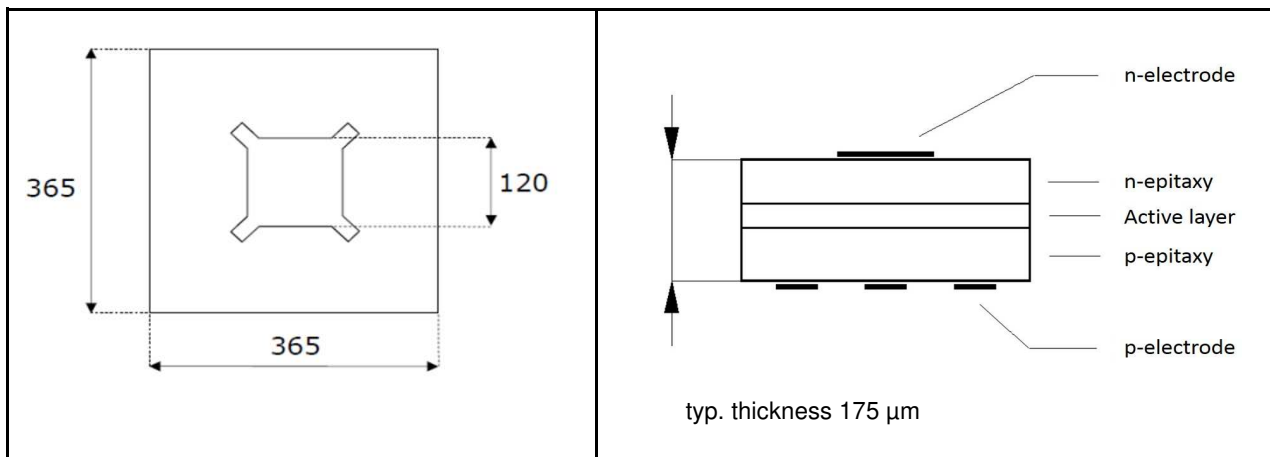
Data Sheet

LED Chip Infrared

EOLC-830-27

Rev. 03, 2018

Radiation	Type	Electrodes
Infrared	AlGaAs/AlGaAs, DDH	n (anode) up



Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F =20 mA	V _F		1.55	1.8	V
Reverse voltage	I _R =10 µA	V _R	5			V
Radiant power*	I _F =20 mA	Φ _e		3.4		mW
Radiant power**	I _F =20 mA	Φ _e		7		mW
Peak wavelength	I _F =20 mA	λ _p	820	830	840	nm
FWHM	I _F =20 mA	Δλ _{0.5}		30		nm
Switching time	I _F =20 mA	t _r , t _f		35		ns

*Measured on bare chip on TO-18 header

**Measured on epoxy covered chip on TO-18 header

Packing

Chips on adhesive film with wire-bond side top

Art. No. xxx xxx



We reserve the right to make changes to improve technical design and may do so without further notice. Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer.